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Method of growing compound semiconductor

Patent Number:

☐ US5399522

Publication date:
1995-03-21

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Requested Patent:
☐ FR2701599

Application Number:
US19930117944 19930908

Priority Number(s):
JP19930050026 19930216

IPC Classification:
H01L21/20

EC Classification:
H01L21/20B6, H01L21/205C2

EC Classification:
H01L21/20B6, H01L21/205C2

Equivalents:
JP3093904B2, ☐ JP6244112

Abstract

A first monocrystalline group III-V compound semiconductor layer is formed on an Si substrate. The surface of the first monocrystalline group III-V compound semiconductor layer is polished. A second monocrystalline group III-V compound semiconductor layer is grown on the polished surface by a metal organic chemical vapor deposition, by using as a group III source material at least partially a source material of group III atoms bonded to ethyl radical at the initial stage of growth, and thereafter by using as the group III source material a source material of group III atoms bonded to methyl radical. A grown layer with a flat surface can be obtained. The surface flatness can be improved further by adding In as a group III element.